

Fig. 2

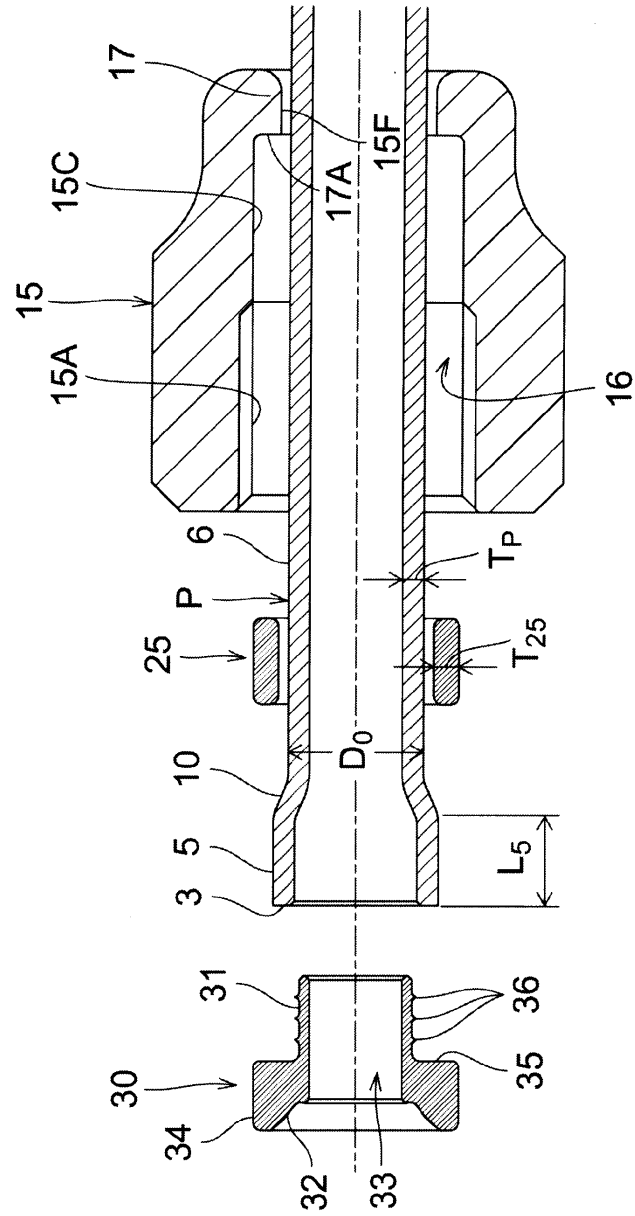


Fig. 4

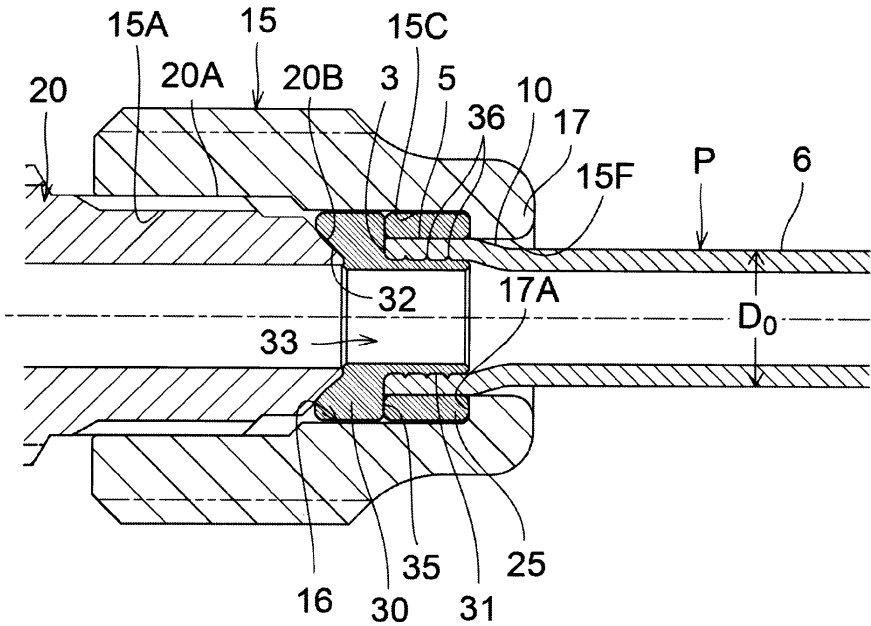


Fig. 5

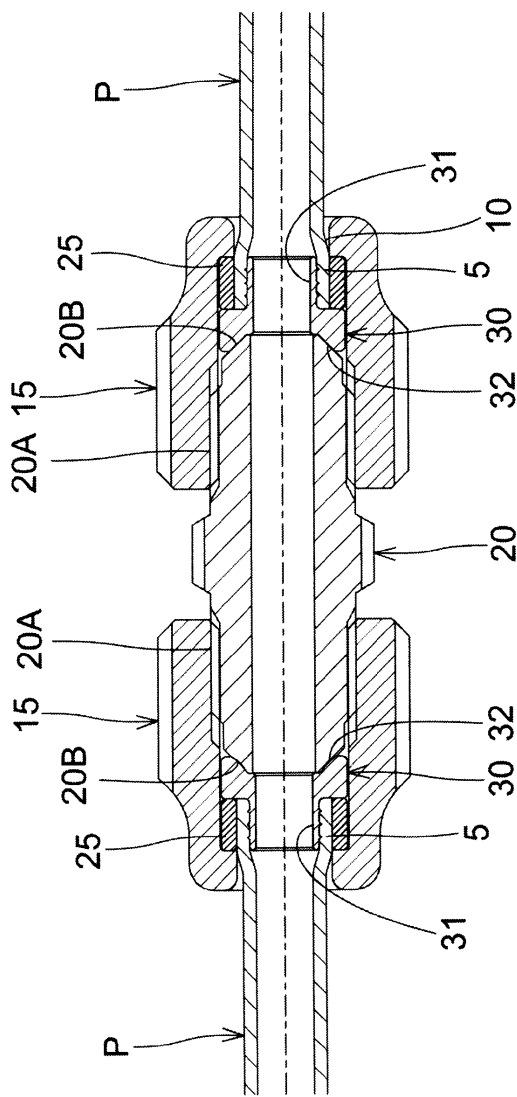


Fig. 6

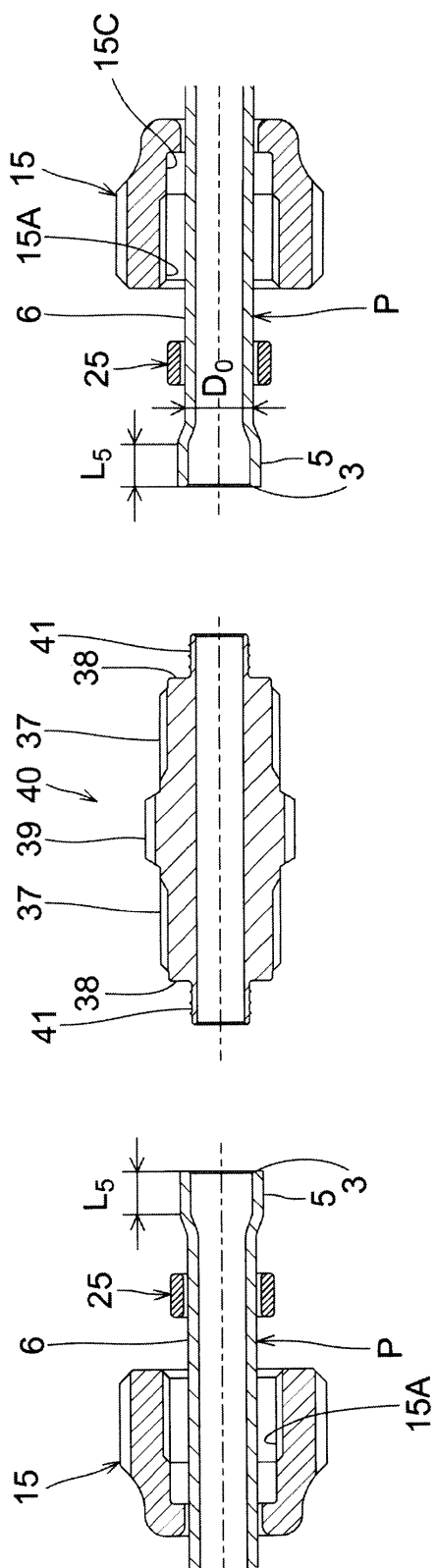
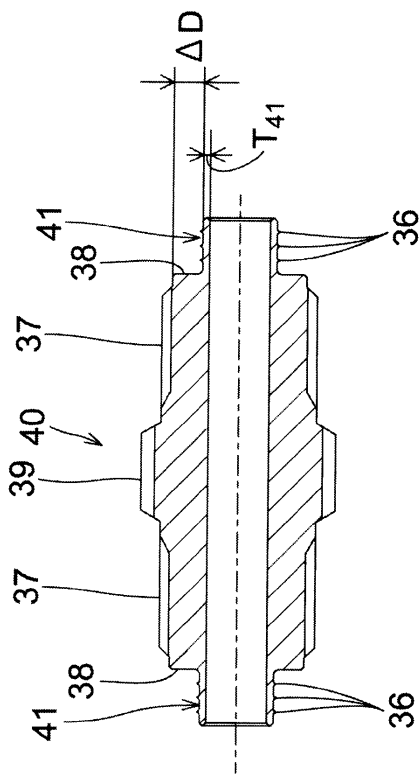


Fig. 7



A cross-sectional view of a multi-layered structure. A central core (40) is shown with a central channel (10). On either side of the core, there are side layers (15) and a bottom layer (5). The side layers (15) are connected to the bottom layer (5) by vertical structures (41). The top surface of the side layers (15) is labeled 25. Arrows labeled 'P' indicate pressure or force applied to the top surface of the side layers (15).

Fig. 1 consists of two cross-sectional views of a semiconductor device.
 (a) shows a central region 40 with a top layer 39, side layers 37, and a bottom layer 41. Dimensions ΔD and T_{41} are indicated.
 (b) shows a cross-section with a substrate 5, a central region 15, and a side region 15A. Dimensions T_{25} , P , and T_p are indicated.

Fig. 13

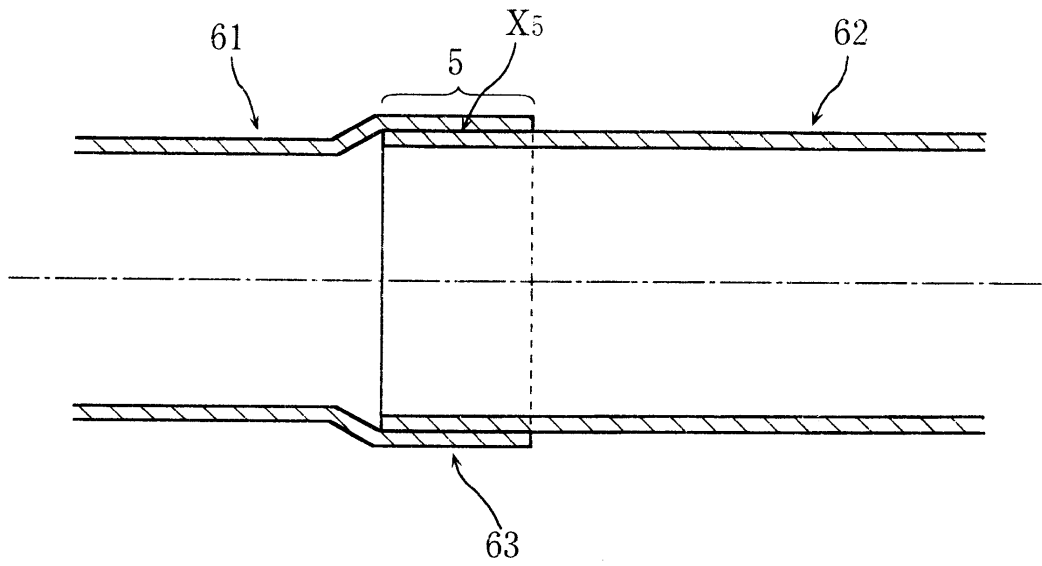


Fig. 14

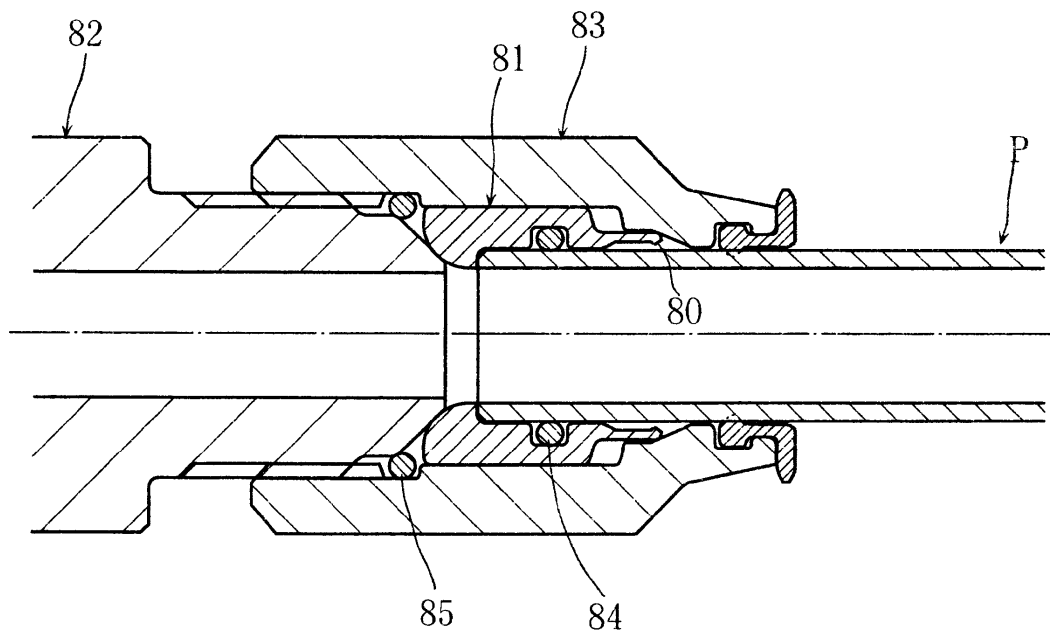


Fig. 15

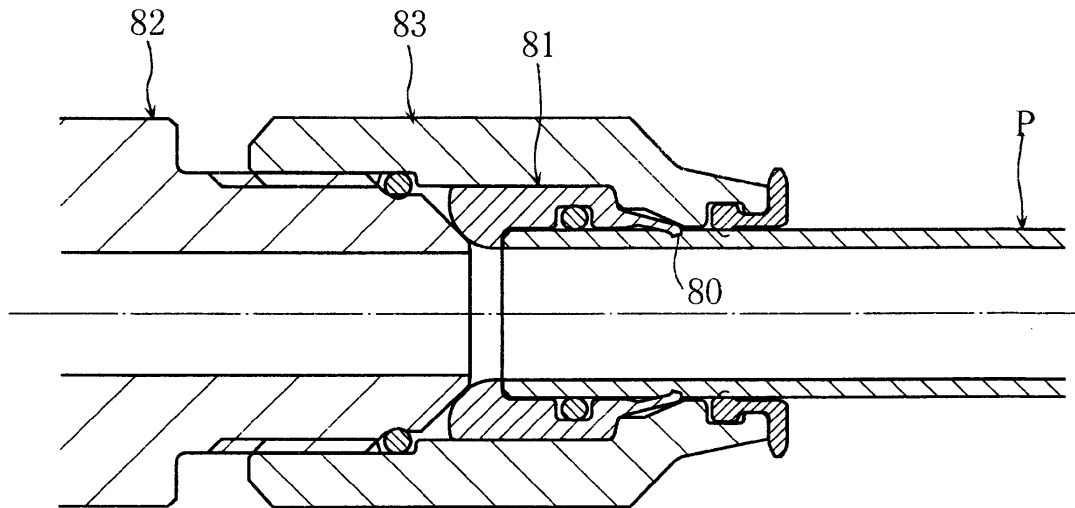


Fig. 16

